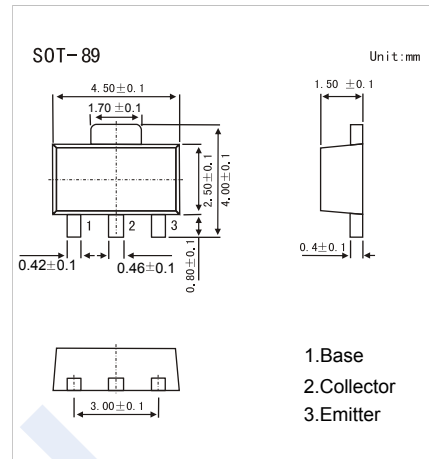


PNP Transistors

2SA1735

■ Features

- Low saturation voltage
- High speed switching time
- Small flat package
- PC = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SC4540



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CE0}	-50	
Emitter - Base Voltage	V _{EB0}	-6	
Collector Current - Continuous	I _c	-1	A
Base Current	I _B	-0.2	
Collector Power Dissipation (Note.1)	P _c	0.5 1	W
Junction Temperature	T _J	150	
Storage Temperature range	T _{stg}	-55 to 150	

Note.1: Mounted on ceramic board (250mm² X 0.8mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c = -1 mA, I _E = 0	-60			V
Collector-emitter breakdown voltage	V _{CE0}	I _c = -10 mA, I _B = 0	-50			
Emitter-base breakdown voltage	V _{EB0}	I _E = -1 mA, I _c = 0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -60 V, I _E = 0			-0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -6 V, I _c = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -500 mA, I _B = -25 mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c = -500 mA, I _B = -25 mA			-1.2	
DC current gain	h _{FE(1)}	V _{CE} = -2V, I _c = -100 mA	120		400	
	h _{FE(2)}	V _{CE} = -2V, I _c = -700 mA	40			
Turn-on Time	t _{on}	See specified Test Circuit		0.1		us
Storage time	t _{stg}			0.25		
Fall time	t _f			0.1		
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		16		pF
Transition frequency	f _T	V _{CE} = -2V, I _c = -100 mA		100		MHz

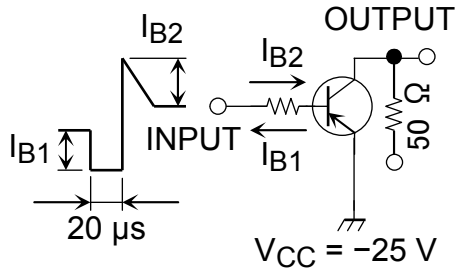
■ Marking

Marking	L°C
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PNP Transistors

2SA1735

Switching Time Test Circuit



$I_{B1} = 25 \text{ mA}, I_{B2} = 25 \text{ mA}$
 DUTY CYCLE $\leq 1\%$

Typical Characteristics

